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In the claims:

- 1. (Currently amended) A method of forming a layer of silicon on a surface of a workpiece comprising the steps of:
- heating said workpiece on a substrate in a vacuum chamber;

depositing a layer of silicon on a surface of said workpiece reacting at least two reactants to form said silicon;

in which said step of heating comprises supplying more than half of a total heating power to a lower surface of said workpiece, whereby said workpiece is maintained at a deposition temperature greater than a crystallization temperature of silicon during the depositing of the layer of silicon.

- 2. (Original) A method according to claim 1, in which said heating power is supplied by an upper set of lamps disposed above said workpiece and a lower set of lamps disposed below said substrate.
- 3. (Original) A method according to claim 2, in which approximately eighty percent of said heating power is supplied to said lower set of lamps.
- 4. (Original) A method according to claim 1, in which said substrate is maintained at a temperature of greater than 690 C.
- 5. (Original) A method according to claim 2, in which said substrate is maintained at a temperature of greater than 690 C.
- 6. (Original) A method according to claim 3, in which said substrate is maintained at a temperature of greater than 690 C.
- 7. (Original) A method according to claim 4, in which said substrate is maintained at a temperature of less than 710 C.

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- 8. (Original) A method according to claim 5, in which said substrate is maintained at a temperature of less than 710 C.
- 9. (Original) A method according to claim 6, in which said substrate is maintained at a temperature of less than 710 C.
- 10. (Original) A method according to claim 1, in which said step of heating comprises supplying more than 75% of a total heating power to a lower surface of said workpiece.
- 11. (Original) A method according to claim 2, in which said step of heating comprises supplying more than 75% of a total heating power to a lower surface of said workpiece.
- 12. (Original) A method according to claim 3, in which said step of heating comprises supplying more than 75% of a total heating power to a lower surface of said workpiece.
- 13. (Original) A method according to claim 4, in which said step of heating comprises supplying more than 75% of a total heating power to a lower surface of said workpiece.
- 14. (Original) A method according to claim 5, in which said step of heating comprises supplying more than 75% of a total heating power to a lower surface of said workpiece.
- 15. (Original) A method according to claim 6, in which said step of heating comprises supplying more than 75% of a total heating power to a lower surface of said workpiece.
- 16. (Original) A method according to claim 7, in which said step of heating comprises supplying more than 75% of a total heating power to a lower surface of said workpiece.

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17. (Original) A method according to claim 8, in which said step of heating comprises supplying more than 75% of a total heating power to a lower surface of said workpiece.

18. to 20. (Withdrawn)